

6600W, 10V - 43V Surface Mount Transient Voltage Suppressor

FEATURES

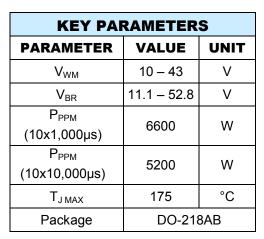
- AEC-Q101 qualified
- Junction passivation optimized design technology
- T_J =175 °C capability suitable for high reliability and automotive requirement
- Moisture sensitivity level: level 1, per J-STD-020
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21
- Meets ISO7637-2 and ISO16750-2 surge specifications (varied by test conditions)
- Meets IEC 61000-4-2 (Level: 4) / ISO 10605 (Level: L4)

Λ	D	D		Λ	TI		N	C
_			_	_		v		J

- Transient Surge Protection.
- Automotive Load Dump Surge Protection.

MECHANICAL DATA

- Case: DO-218AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: Uni-directional
- Weight: 2.691g (approximately)







DO-218AB



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)							
PARAMETER	SYMBOL	VALUE	UNIT				
Non-repetitive peak impulse power dissipation with 10/1000µs waveform	P _{PPM}	6600	W				
Non-repetitive peak impulse power dissipation with 10/10000µs waveform (1)	P _{PPM}	5200	W				
Steady state power dissipation (Fig.1)	P_D	8	W				
Forward Voltage at I _F =100 A ⁽²⁾	$V_{F,MAX}$	1.8	V				
Peak forward surge current, 8.3 ms single half sine-wave	I _{FSM}	700	Α				
Junction temperature	T_J	-55 to +175	°C				
Storage temperature	T _{STG}	-55 to +175	°C				

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Notes

- 1. Non-repetitive current pulse per Fig. 3.
- 2. Pulse test with PW=0.3 ms



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THERMAL PERFORMANCE							
PARAMETER	SYMBOL	TYP	TINU				
Junction-to-case thermal resistance per diode	$R_{\Theta JC}$	0.8	°C/W				

Thermal Performance Note: With ideal heatsink

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)										
Part number	Marking code	volt V _{BR} (\	adown tage at I _T /) te 1)	Test current I _T (mA)	Working stand-off voltage V _{WM} (V)	Maximum blocking leakage current I _R at V _{WM} (µA)	Maximum blocking leakage current I _R at V _{WM} T _J =175°C	Maximum peak impulse current I _{PPM} (A) tp	Maximum clamping voltage V _C at I _{PPM} (V)	Typical temp. coefficient of V _{BR} αT (%/°C)
		Min.	Max.			(Note 1)	(µA) (Note 1)	=10/1000 (µs)		(Note 2)
TLD8S10AH	TLD8S10A	11.1	12.3	5.0	10.0	15	250	388	17.0	0.069
TLD8S11AH	TLD8S11A	12.2	13.5	5.0	11.0	10	150	363	18.2	0.072
TLD8S12AH	TLD8S12A	13.3	14.7	5.0	12.0	10	150	332	19.9	0.074
TLD8S13AH	TLD8S13A	14.4	15.9	5.0	13.0	10	150	307	21.5	0.076
TLD8S14AH	TLD8S14A	15.6	17.2	5.0	14.0	10	150	284	23.2	0.078
TLD8S15AH	TLD8S15A	16.7	18.5	5.0	15.0	10	150	270	24.4	0.080
TLD8S16AH	TLD8S16A	17.8	19.7	5.0	16.0	10	150	254	26.0	0.081
TLD8S17AH	TLD8S17A	18.9	20.9	5.0	17.0	10	150	239	27.6	0.082
TLD8S18AH	TLD8S18A	20.0	22.1	5.0	18.0	10	150	226	29.2	0.083
TLD8S20AH	TLD8S20A	22.2	24.5	5.0	20.0	10	150	204	32.4	0.085
TLD8S22AH	TLD8S22A	24.4	26.9	5.0	22.0	10	150	186	35.5	0.086
TLD8S24AH	TLD8S24A	26.7	29.5	5.0	24.0	10	150	170	38.9	0.087
TLD8S26AH	TLD8S26A	28.9	31.9	5.0	26.0	10	150	157	42.1	0.088
TLD8S28AH	TLD8S28A	31.1	34.4	5.0	28.0	10	150	145	45.4	0.089
TLD8S30AH	TLD8S30A	33.3	36.8	5.0	30.0	10	150	136	48.4	0.090
TLD8S33AH	TLD8S33A	36.7	40.6	5.0	33.0	10	150	124	53.3	0.091
TLD8S36AH	TLD8S36A	40.0	44.2	5.0	36.0	10	150	114	58.1	0.091
TLD8S40AH	TLD8S40A	44.4	49.1	5.0	40.0	10	150	102	64.5	0.092
TLD8S43AH	TLD8S43A	47.8	52.8	5.0	43.0	10	150	95.1	69.4	0.093

Note:

- 1. Pulse test with PW=30 ms
- 2. To calculate V_{BR} vs. junction temperature, use the following formula: V_{BR} at T_J = V_{BR} at 25 °C x (1 + α T x (T_J 25))

ORDERING INFORMATION						
ORDERING CODE (Note)	PACKAGE	PACKING				
TLD8SxxAH MAG	DO-218AB	750 / 13" Plastic reel				

Note: "xx" defines voltage from 10V (TLD8S10AH) to 43V (TLD8S43AH)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Power Derating Curve

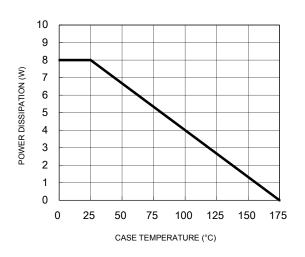


Fig.3 Clamping Power Pulse Waveform

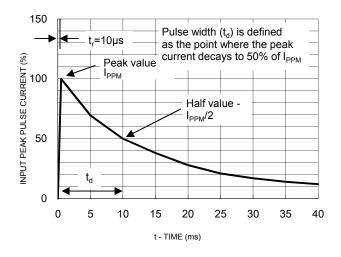


Fig.5 Typical Transient Thermal Impedance

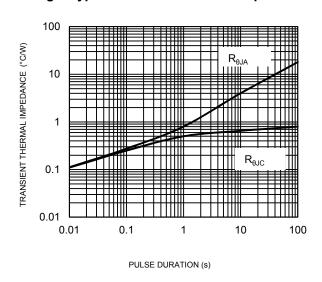


Fig.2 Load Dump Power Characteristics (10ms Exponential Waveform)

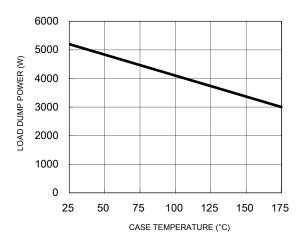


Fig.4 Reverse Power Capability

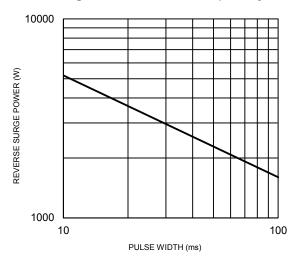
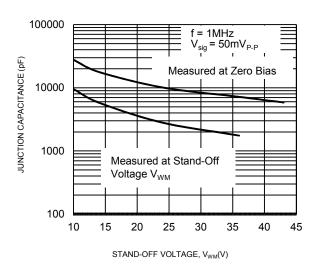


Fig.6 Typical Junction Capacitance

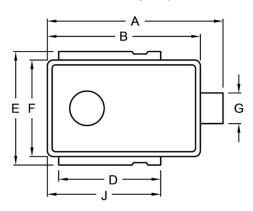


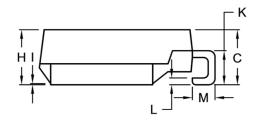




PACKAGE OUTLINE DIMENSIONS

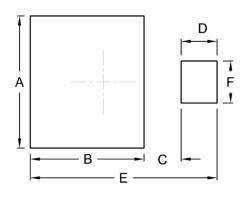
DO-218AB





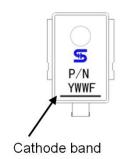
DIM.	Unit	(mm)	Unit (inch)		
DIW.	Min.	Max.	Min.	Max.	
Α	15.00	16.00	0.591	0.630	
В	13.30	13.70	0.524	0.539	
С	4.70	5.50	0.185	0.217	
D	8.70	9.30	0.343	0.366	
E	9.50	10.50	0.374	0.413	
F	8.30	8.70	0.327	0.343	
G	2.40	3.00	0.094	0.118	
Н	4.70	5.00	0.185	0.197	
ı	0.00	0.10	0.000	0.004	
J	9.70	10.30	0.382	0.406	
K	2.50	3.50	0.098	0.138	
L	0.50	0.70	0.020	0.028	
М	1.50	2.50	0.059	0.098	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	11.00	0.433
В	9.50	0.374
С	3.10	0.122
D	3.00	0.118
E	15.60	0.614
F	3.50	0.138

MARKING DIAGRAM



P/N = Marking Code YWW = Date Code F = Factory Code



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